

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claim 1 (Currently Amended): A method of storing data comprising:

connecting a data line to a first sense amplifier when a first bit line is disconnected from the first sense amplifier;

connecting the first sense amplifier to the first bit line when the data line is disconnected from the first sense amplifier; and

connecting the data line to a second sense amplifier when the first bit line is connected to the first sense amplifier,

wherein the first bit line is connected to the first sense amplifier via a switching transistor, and wherein the switching transistor is driven to be on [[by]] during a writing operation by a first signal that changes between a ground level and a first voltage, and is then driven to be on [[by]] after the writing operation by a second signal that changes between the ground level and a second voltage, the second voltage [[which]] is higher than the first voltage.

Claim 2 (Canceled)

Claim 3 (Original): The method of claim 1, further comprising connecting the second sense amplifier to a second bit line when the second sense amplifier is disconnected from the data line.

Claim 4 (Original): The method of claim 3, wherein the second bit line is included in a memory cell array block that is different from a memory cell array block in which the first bit line is included.

Claims 5-7 (Canceled)

Claim 8 (Currently Amended): A method of storing data comprising:

transferring first data from a data line to a first sense amplifier when a first bit line is disconnected from the first sense amplifier;

transferring the first data from the first sense amplifier to the first bit line after the first sense amplifier is disconnected from the data line;

transferring second data from the data line to a second sense amplifier when the first bit line is connected to the first sense amplifier; and

transferring the second data from the second sense amplifier to a second bit line after the second sense amplifier is disconnected from the data line,

wherein the first data is transferred from the first sense amplifier to the first bit line via a switching transistor, wherein the switching transistor is driven during a writing

operation by a first signal that changes between a ground level and a first voltage, and is then driven after the writing operation by a second signal that changes between the ground level and a second voltage, the second voltage is higher than the first voltage.

Claim 9 (Original): The method of claim 8, wherein the second bit line is included in a memory cell array block that is different from a memory cell array block in which the first bit line is included.

Claims 10-12 (Canceled)

Claim 13 (Currently Amended): A method of storing data comprising:

transferring first data from a data line to a first sense amplifier, wherein the first data is latched in the first sense amplifier;

transferring the first data from the first sense amplifier to a first bit line; and

transferring second data from the data line to a second sense amplifier, wherein the second data is latched in the second sense amplifier,

wherein a period of latching the second data from the data line to the second sense amplifier, and a period of transferring the first data from the first sense amplifier to the first bit line, are overlapped,

wherein the first data is transferred from the first sense amplifier to the first bit line via a switching transistor, wherein the switching transistor is driven by a first signal

that changes between ground level and a first voltage, and is then driven by a second signal that changes between the ground level and a second voltage, the second voltage is higher than the first voltage.

Claim 14 (Original): The method of claim 13, wherein the second bit line is included in a memory cell array block that is different from a memory cell array block in which the first bit line is included.

Claims 15-17 (Canceled)

Claim 18 (Currently Amended): A method of transferring data comprising:

supplying a first signal that changes between a ground level and a first voltage to a switching transistor which is connected between a sense amplifier and a bit line, wherein data having a voltage drop caused by a threshold voltage of the switching transistor is transferred from the sense amplifier to the bit line by the switching transistor responsive to the first voltage; and

supplying a second signal that changes between the ground level and a second voltage ~~which is higher than the first voltage~~ to the switching transistor, wherein the data which does not have a voltage drop caused by the threshold voltage of the switching transistor is transferred from the sense amplifier to the bit line responsive to the second voltage, the second voltage is higher than the first voltage.

Claim 19 (Canceled)